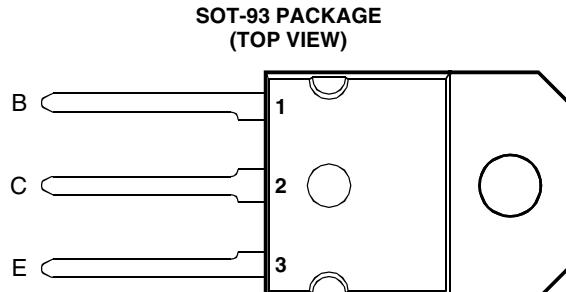


- Designed for Complementary Use with TIP145, TIP146 and TIP147
- 125 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- Minimum h_{FE} of 1000 at 4 V, 5 A



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP140	V_{CBO}	60	V
	TIP141	V_{CBO}	80	
	TIP142	V_{CBO}	100	
Collector-emitter voltage ($I_B = 0$)	TIP140	V_{CEO}	60	V
	TIP141	V_{CEO}	80	
	TIP142	V_{CEO}	100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	10	A
Peak collector current (see Note 1)		I_{CM}	15	A
Continuous base current		I_B	0.5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	125	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	100	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.

2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 5$ mA, $R_{BE} = 100$ Ω, $V_{BE(off)} = 0$, $R_S = 0.1$ Ω, $V_{CC} = 20$ V.

PRODUCT INFORMATION

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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT	
$V_{(BR)CEO}$	Collector-emitter breakdown voltage (see Note 5)	$I_C = 30 \text{ mA}$	$I_B = 0$	TIP140 TIP141 TIP142	60 80 100			V
I_{CEO}	Collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 40 \text{ V}$ $V_{CE} = 50 \text{ V}$	$I_B = 0$	TIP140 TIP141 TIP142		2 2 2	mA	
I_{CBO}	Collector cut-off current	$V_{CB} = 60 \text{ V}$ $V_{CB} = 80 \text{ V}$ $V_{CB} = 100 \text{ V}$	$I_E = 0$	TIP140 TIP141 TIP142		1 1 1	mA	
I_{EBO}	Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$			2	mA	
h_{FE}	Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 5 \text{ A}$ $I_C = 10 \text{ A}$	(see Notes 5 and 6)	1000 500			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = 10 \text{ mA}$ $I_B = 40 \text{ mA}$	$I_C = 5 \text{ A}$ $I_C = 10 \text{ A}$	(see Notes 5 and 6)		2 3	V	
V_{BE}	Base-emitter voltage	$V_{CE} = 4 \text{ V}$	$I_C = 10 \text{ A}$	(see Notes 5 and 6)		3	V	
V_{EC}	Parallel diode forward voltage	$I_E = 10 \text{ A}$	$I_B = 0$	(see Notes 5 and 6)		3.5	V	

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on}	Turn-on time	$I_C = 10 \text{ A}$	$I_{B(on)} = 40 \text{ mA}$	$I_{B(off)} = -40 \text{ mA}$	0.9		μs
t_{off}	Turn-off time	$V_{BE(off)} = -4.2 \text{ V}$	$R_L = 3 \Omega$	$t_p = 20 \mu\text{s}$, dc $\leq 2\%$	11		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PRODUCT INFORMATION

TYPICAL CHARACTERISTICS

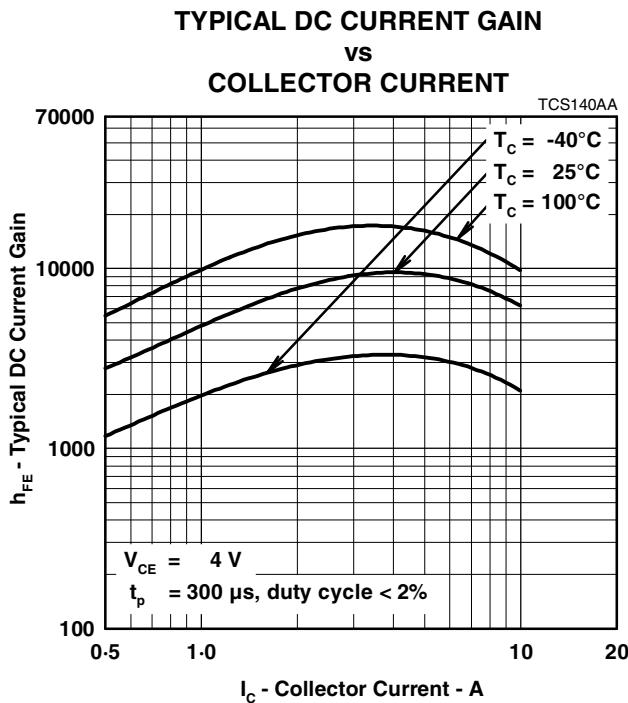


Figure 1.

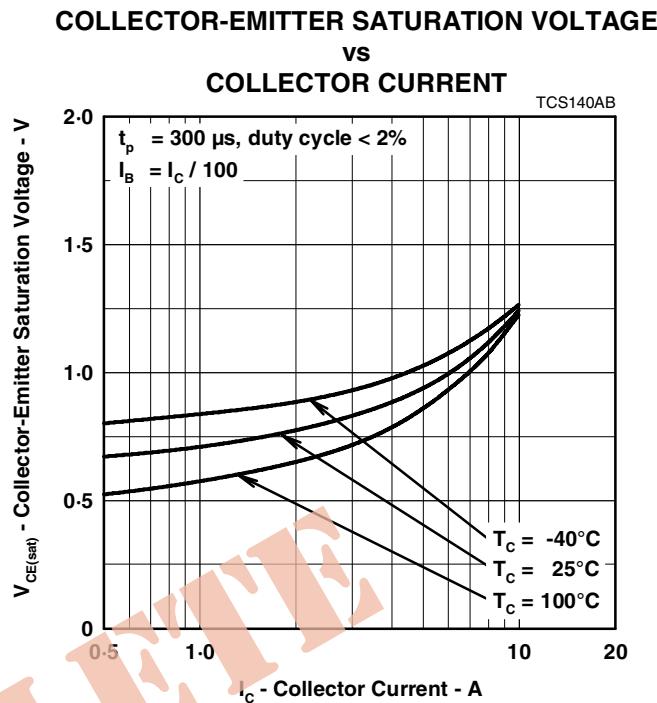


Figure 2.

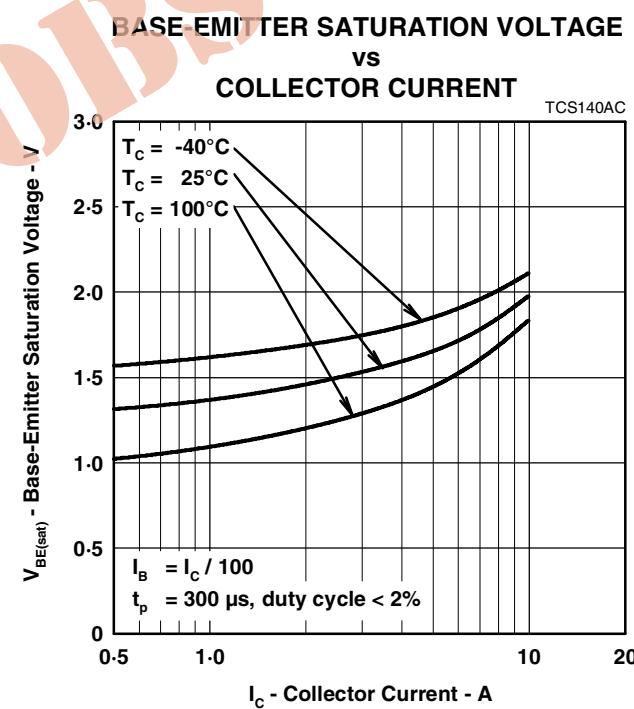


Figure 3.

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MAXIMUM SAFE OPERATING REGIONS

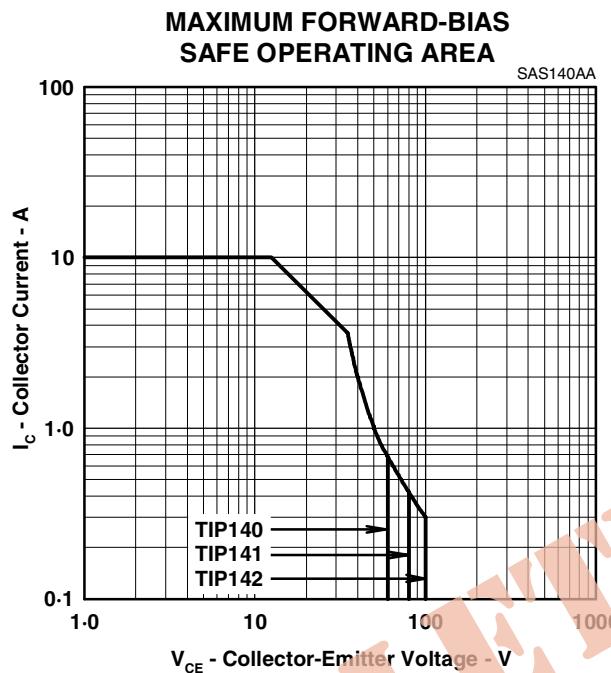


Figure 4.

THERMAL INFORMATION

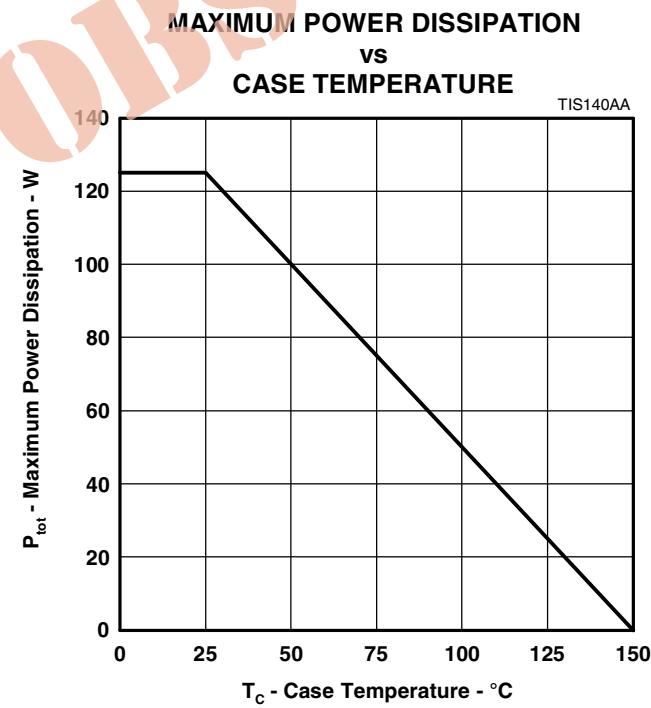


Figure 5.

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